

F1G. 7

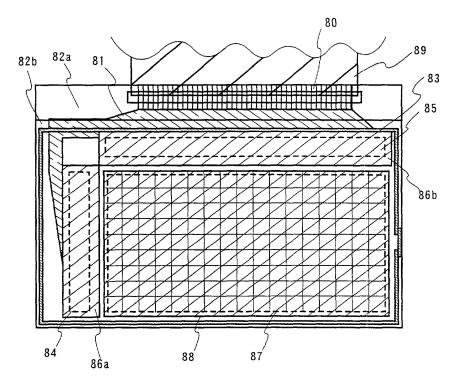


FIG. 8

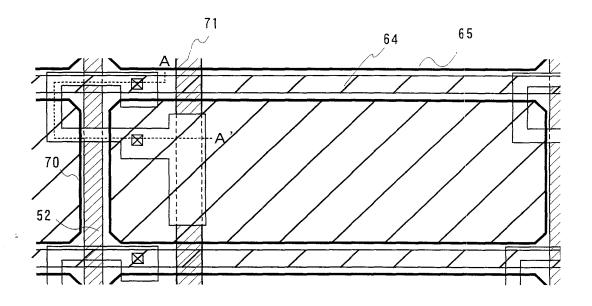


FIG. 9A

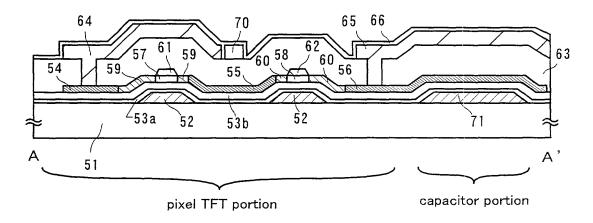
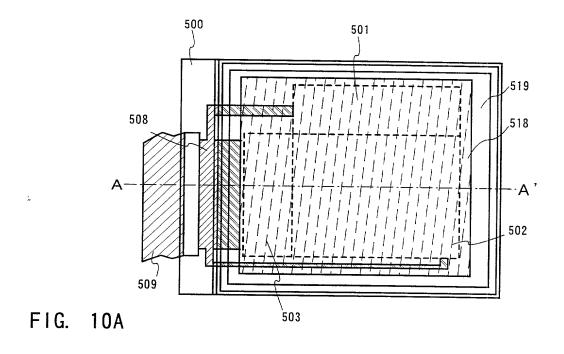
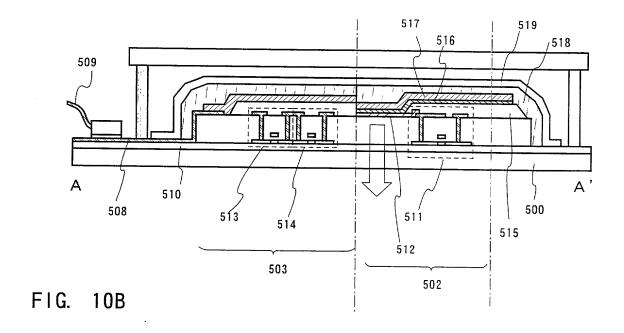


FIG. 9B





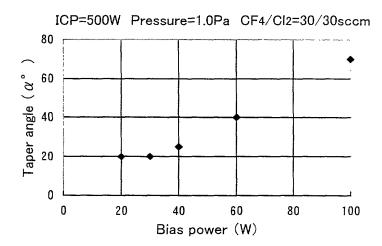


FIG. 11 Dependence of taper angle on bias power.

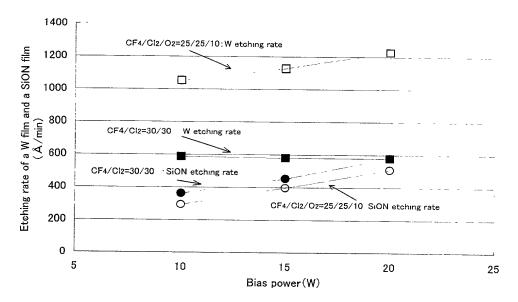


FIG. 12 Dependence of an etching rate of a W film and an SiON film on bias power.

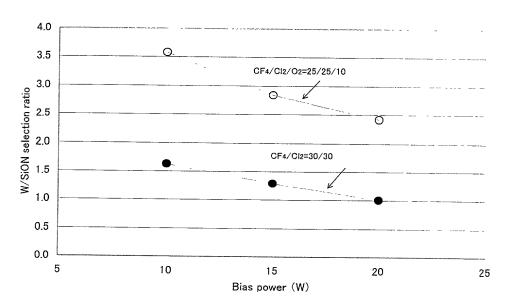


FIG. 13 Dependence of a selection ratio between a W film and an SiON film on a bias power.

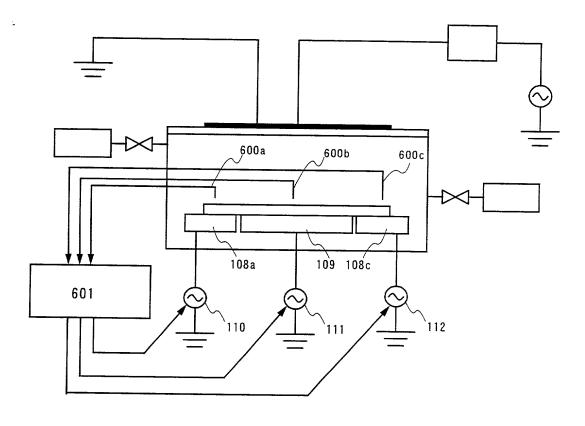


FIG. 14

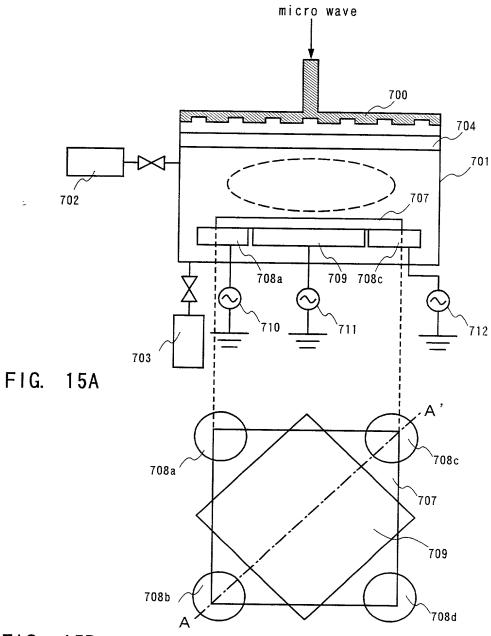


FIG. 15B

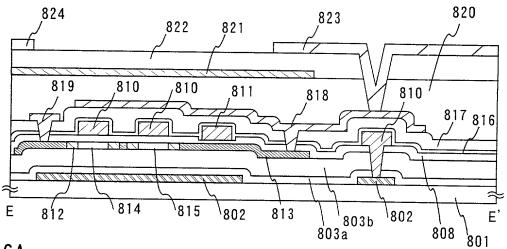


FIG. 16A

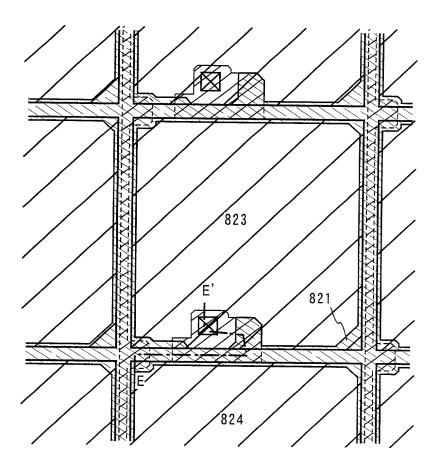


FIG. 16B

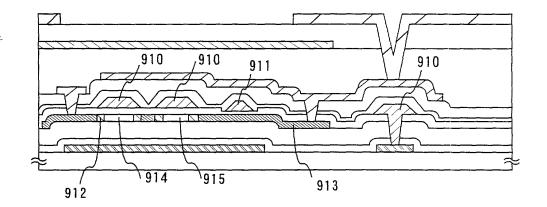


FIG. 17

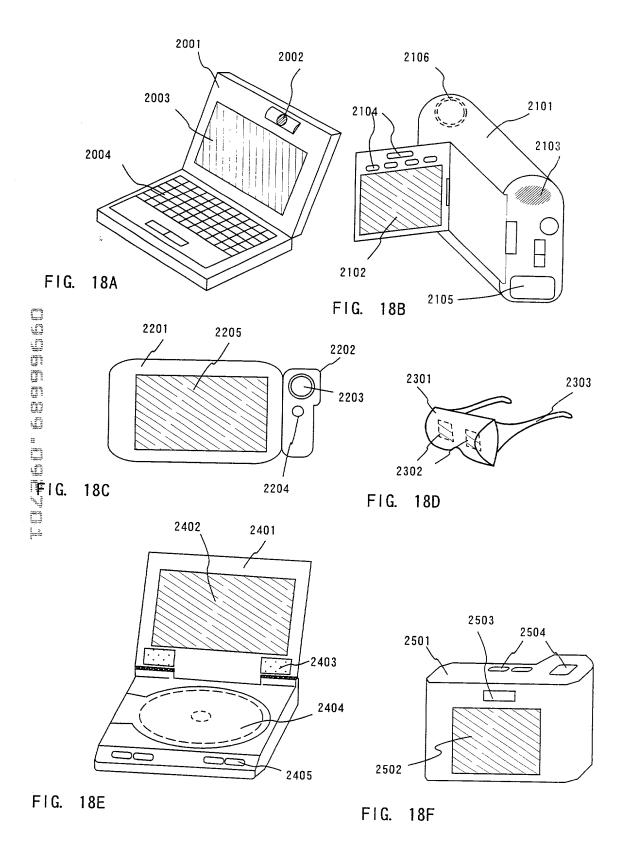
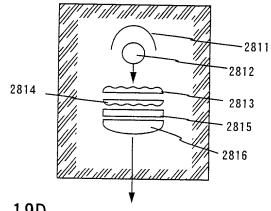


FIG. 19C

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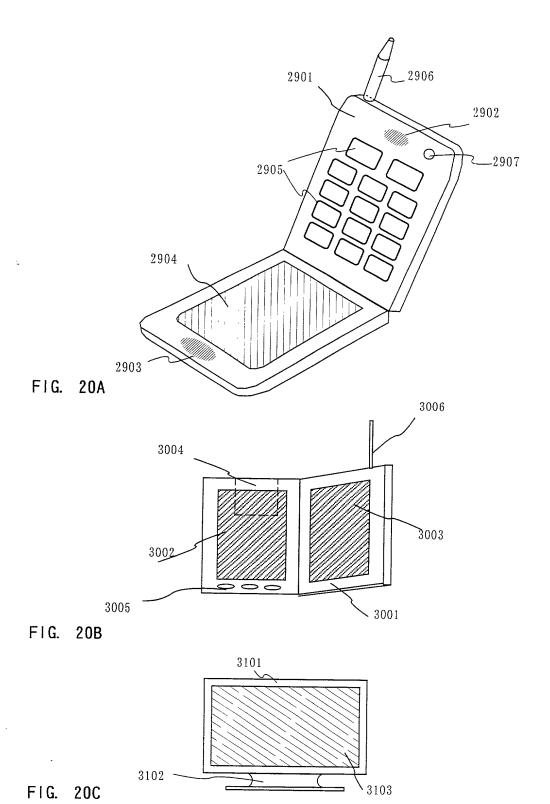


`2803[´]

2802

FIG. 19D

2804



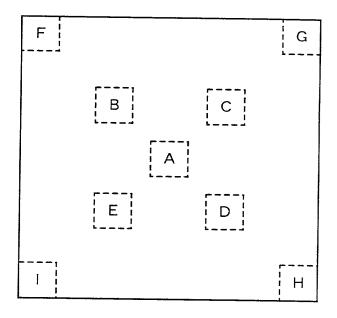


FIG. 21A

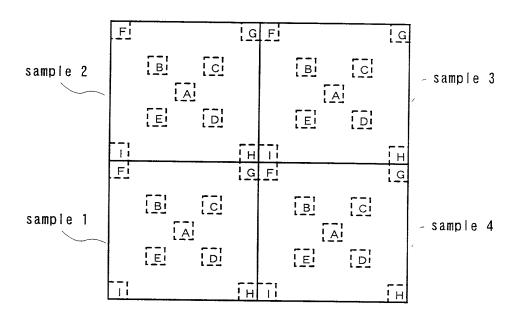


FIG. 21B